2SC1360, 2SC1360A

Silicon NPN epitaxial planar type

For intermediate frequency amplification of TV image

Symbol

V_{CBO}

V_{CEO}

V_{EBO}

 I_C

 P_C

Ti

T_{stg}

Rating

50

60

45

60

4

50

1

150

-55 to +150

Unit V

v

V

mA W

°C

°C

Features

- High transition frequency f_T
- \bullet Large collector power dissipation P_{C}

Parameter

Emitter-base voltage (Collector open)

Collector-base voltage (Emitter open)

Collector-emitter voltage

Collector power dissipation

(Base open)

Collector current

Junction temperature

Storage temperature

<u>5.9±0.2</u>	Unit: mm
	8.6 ±0.2
0.7±0.1	13.510.5
	0.45 ⁺⁰²
<u>0.45^{+0.2} (1.27)</u> (1	<u>27)</u> 1: Emitter
	2: Collector 3: Base
2.	EIAJ: SC-51 TO-92L-A1 Package

Absolute Maximum Ratings $T_a = 25^{\circ}C$

2SC1360

2SC1360A

2SC1360

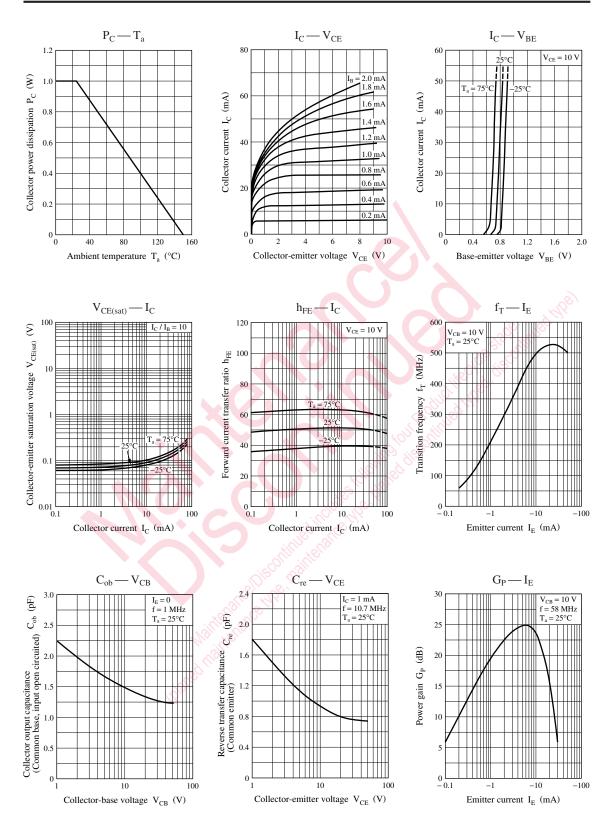
2SC1360A

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	U	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage	2SC1360	V _{CBO}	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	50			V
(Emitter open)	2SC1360A		in the state	60			
Collector-emitter voltage	2SC1360	V _{CEO}	$I_{\rm C} = 3 \text{ mA}, I_{\rm B} = 0$	45			V
(Base open)	2SC1360A		$I_C = 1 \text{ mA}, I_B = 0$	60			
Emitter-base voltage (Colle	ctor open)	V _{EBO}	$I_{\rm E} = 100 \ \mu A, \ I_{\rm C} = 0$	4			V
Collector-base cutoff current (E	mitter open)	I _{CBO}	$V_{CB} = 20 V, I_E = 0$			100	nA
Forward current transfer rat	io 👋	h _{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$	20	50	100	_
Collector-emitter saturation	voltage	V _{CE(sat)}	$I_{C} = 20 \text{ mA}, I_{B} = 2 \text{ mA}$			0.4	V
Transition frequency	2SC1360	f _T	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 100 \text{ MHz}$	300	500		MHz
	2SC1360A			300			
Reverse transfer capacitance	2SC1360	C _{re}	$V_{CB} = 10 \text{ V}, I_E = -1 \text{ mA}, f = 10.7 \text{ MHz}$		0.96	1.5	pF
(Common emitter)	2SC1360A					1.5	
Power gain	2SC1360	G _P	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 58 \text{ MHz}$	22	26	30	dB
	2SC1360A]		22		30	

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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